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### 3A Boost Converter for High Brightness LED Driver with Multiple Dimming Methods

Check for Samples: TPS61500

### FEATURES

- 2.9-V to 18-V Input Voltage Range
- 3-A, 40-V Internal Power Switch
  - Four 3-W LEDs from 5-V input
  - Eight 3-W LEDs from 12-V input
- High Efficiency Power Conversion: Up to 93%
- Frequency Set by External Resistor: 200-kHz to 2.2-MHz
- User Defined Soft Start into Full Load
- Programmable Over Voltage Protection

#### DESCRIPTION

- Analog and Pure PWM Brightness Dimming
- 14-pin HTSSOP Package with PowerPAD™

### APPLICATIONS

- Monitor backlight
- 1-W or 3-W high brightness LED

The TPS61500 is a monolithic switching regulator with integrated 3-A, 40-V power switch. It is an ideal driver for high brightness 1-W or 3-W LED. The device has a wide input voltage range to support application with input voltage from multi-cell batteries or regulated 5-V, 12-V power rails.

The LED current is set with an external sensor resistor R3, and the feedback voltage that is regulated to 200-mV by current mode PWM (pulse width modulation) control loop, as shown in the typical application. The device supports analog and pure PWM dimming methods for LED brightness control. Connecting a capacitor to the DIMC pin configures the device to be used for analog dimming, and the LED current varies proportional to the duty cycle of an external PWM signal. Floating the DIMC pin configures the IC for pure PWM dimming with the average LED current being the PWM signal's duty cycle times a set LED current.

The device features a programmable soft-start function to limit inrush current during start-up, and has built-in other protection features, such as pulse-by-pulse over current limit, over voltage protection and thermal shutdown. The TPS61500 is available in 14-pin HTSSOP package with PowerPad.

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### **TPS61500**

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### **TYPICAL APPLICATION**







Figure 2. Pure PWM Dimming Method

Table 1.	ORDERING	INFORMATION <sup>(1)</sup> (	2)
i apie i.	URDERING		

T <sub>A</sub>	PART NUMBER	PACKAGE	PACKAGE MARKING
-40°C to 85°C	TPS61500	HTSSOP-14	61500

(1) For the most current package and ordering information, see the TI WEB site at www.ti.com

(2) The PWP package is available in tape and reel. Add R suffix (TPS61500PWPR) to order quantities of 2000 parts per reel. Without suffix, the TPS61500PWP is shipped in tubes with 90 parts per tube.



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#### **ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

over operating free-air temperature range (unless otherwise noted)

	VALUE	UNIT
Supply voltages on pin VIN <sup>(2)</sup>	-0.3 to 20	V
Voltages on pins EN <sup>(2)</sup>	ages on pins EN <sup>(2)</sup> -0.3 to 20	
Voltage on pin FB, FREQ and COMP, OVP <sup>(2)</sup>	–0.3 to 3	V
Voltage on pin DIMC, SS <sup>(2)</sup>	–0.3 to 7	V
Voltage on pin SW <sup>(2)</sup>	-0.3 to 40	V
Continuous power dissipation	See the Thermal Information Table	
Operating junction temperature range -40 to 150		°C
Storage temperature range	-65 to 150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

#### **THERMAL INFORMATION**

	THEDMAL METDIC(1)	TPS61500	
		PWP 14 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance	45.2	
θ <sub>JCtop</sub>	Junction-to-case (top) thermal resistance	34.9	]
$\theta_{JB}$	Junction-to-board thermal resistance	30.1	°C/M
ΨJT	Junction-to-top characterization parameter	1.5	0/00
$\Psi_{JB}$	Junction-to-board characterization parameter	29.9	]
θ <sub>JCbot</sub>	Junction-to-case (bottom) thermal resistance	5.8	]

# (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953. **RECOMMENDED OPERATING CONDITIONS**

		MIN	NOM MAX	UNIT
V <sub>IN</sub>	Input voltage range	2.9	18	V
Vo	Output voltage range	V <sub>IN</sub>	38	V
L	Inductor <sup>(1)</sup>	4.7	47	μH
CI	Input Capacitor	4.7		μF
Co	Output Capacitor	4.7	10	μF
Cdim	Analog dimming capacitor <sup>(2)</sup>	0.1		μF
PWM	Analog and PWM dimming frequency <sup>(3)</sup>	200	1000	Hz
T <sub>A</sub>	Operating ambient temperature	-40	85	°C
TJ	Operating junction temperature	-40	125	°C

(1) The inductance value depends on the switching frequency and end applications. While larger values may be used, values between 4.7μH and 47μH have been successfully tested in various appliations. Refer to the Inductor Selection for detail.

(2) The Cdim with the internal resistor (25kΩ TYP) forms a RC filter that generates the FB reference voltage according to the duty cycle of PWM signal. To optimize the RC filter and reduce the output ripple, the value larger than 0.1µF of Cdim is recommended.

(3) When analog dimming, the max PWM frequency is set by on the RC filter to optimize the output ripple. When PWM dimming, the PWM frequency is set by the IC loop response.



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#### **ELECTRICAL CHARACTERISTICS**

FSW = 1.2MHz (Rfreq =  $80k\Omega$ ), Vin = 3.6V, CRTL = Vin, T<sub>A</sub> =  $-40^{\circ}$ C to  $85^{\circ}$ C, typical values are at T<sub>A</sub> =  $25^{\circ}$ C (unless otherwise noted)

SUPPLY CURRENT         2.9         1.8         V           Van         Input voltage idescent current into Vin e3.6V         Device PVM switching without load.Vin e3.6V         3.5         mA           Vgn_D         Derider PVM switching without load.Vin e3.6V         1.5         µA           VuvLO         Under-voltage lockout threshold         V <sub>N</sub> falling         2.5         2.7         V           Vma         Under-voltage lockout threshold         V <sub>N</sub> falling         2.5         2.7         V           Vma         Under-voltage lockout threshold         V <sub>N</sub> falling         2.5         2.7         V           Vma         Under-voltage lockout threshold         V <sub>N</sub> falling         2.5         2.7         V           Vma         Under-voltage lockout threshold         V <sub>N</sub> falling         2.5         2.7         V           Vma         Under-voltage lockout threshold         V <sub>N</sub> falling         1.2         V         V         V           Rem         Noldage feedback regulation voltage         N         2.9         V         V         V           Vgr         Voltage feedback regulation voltage         195         200         nA         V           Vgr         Voltage feedback regulation voltage         N         PA </th <th></th> <th>PARAMETER</th> <th>TEST CONDITIONS</th> <th>MIN</th> <th>TYP</th> <th>MAX</th> <th>UNIT</th>		PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Vag         Input voltage range         2.9         18         V           Ig         Operating quiescent current into Vin         Device VMIs witching without load,Vin         3.5         mA           Ign         Shutdown current         EN = GND, Vin = 3.6 V         1.5         µA           Vinco         Under-voltage lockout threshold         Vin falling         2.5         7         V           Vinco         Under-voltage lockout threshold         Vin falling         2.5         7         V           Vinco         Under-voltage lockout threshold         Vin falling         2.5         7         V           Vinco         Under-voltage lockout threshold         Vin falling         2.5         7         V           Vinco         Under-voltage lockout threshold         Vin falling         1.2         V         V           Vinco         Under-voltage lockout threshold         Vin = 2.9 V to 18 V         1.2         V         V           Vina         EN biolic high voltage         Vin = 2.9 V to 18 V         1.2         V         Mod         V           Vingt         Vindtage feedback regulation voltage         EN high to low         10         mV         Mad         V         V           Vigt         Vingt	SUPPLY CUR	RENT					
b_a         Operating quiescent current into Vin solv         Device PVM switching without load,Vin Solv         ····································	V <sub>IN</sub>	Input voltage range		2.9		18	V
Ign         Shutdown current         EN = GND, Vin = 3.6 V         ······.1.5         μA           V <sub>VVLO</sub> Under-voltage lockout hysteresis         130         mV           ENABLE AND REFERENCE CONTROL         130         mV           V <sub>prig</sub> Under-voltage lockout hysteresis         130         V           V <sub>prig</sub> EN logic high voltage         Vin = 2.9 V to 18 V         1.2         V           V <sub>prig</sub> Dunder-voltage lockout hysteresis         400         800         1600         KQ           R <sub>n</sub> EN logic high voltage         Vin = 2.9 V to 18 V         1.2         V         V           V <sub>pris</sub> Shutdown delay, SS discharge         EN high to low         10         mrs         V           V <sub>ME</sub> Voltage feedback regulation voltage         195         200         205         mV           V <sub>BE</sub> Voltage feedback regulation voltage         195         200         nA         yA           V <sub>Back</sub> Comp pin situ current         V <sub>FB</sub> = V <sub>BEF</sub> +200 mV, V <sub>COMP</sub> = 1 V         40         µA           V <sub>Back</sub> Comp pin inthe shold         Duty cycle = 0%         0.95         V           V <sub>CCLP</sub> Comp pin inthreshold         Duty cycle = 0%         0.16<	l <sub>Q</sub>	Operating quiescent current into Vin	Device PWM switching without load,Vin =3.6V			3.5	mA
Vivuo         Under-voltage lockout hysteresis         Vin         Statistical Statisti	I <sub>SD</sub>	Shutdown current	EN = GND, Vin = 3.6 V			1.5	μA
Vhysis         Under voltage lockout hysteresis         130         mV           ENABLE AND REFERENCE CONTROL         Vin = 2.9 V to 18 V         1.2         V           Varia         EN logic high voltage         Vin = 2.9 V to 18 V         1.2         V.4         V           Varia         EN logic high voltage         Vin = 2.9 V to 18 V         10         V.4         V           Varia         EN logic high voltage         EN high to low         10         V.4         V           Varia         EN puil down resistor         400         800         1600         kG           Varia         EN puil down resistor         195         200         205         mV           Varia         Voltage feedback regulation voltage         -100         0         10         mV           Veg.ore         Error amplifier offset         -100         0         mV         µA           Voctar         Comp pin sink current         VFB = VREF+200 mV, VCOMP = 1 V         40         µA           Voctar         Comp pin source current         VFB = VREF+200 mV, VCOMP = 1 V         40         µA           Voctar         Comp pin fink reschold         Duty cycle = 0%         0.95         V           Vortar         Comp pin threshold	V <sub>UVLO</sub>	Under-voltage lockout threshold	V <sub>IN</sub> falling		2.5	2.7	V
ENABLE AND REFERENCE CONTROLVanh.EN logic lingh voltageVin = 2.9 V to 18 V1.2VRan.EN logic low voltageVin = 2.9 V to 18 V0.4 VRan.EN pull down resistor4008001600kΩTattShutdown delay, SS dischargeEN high to low10msVoltage feedback regulation voltageVoltage feedback regulation voltage195200205mVVage, rVoltage feedback regulation voltage100010mVVage, rComp pin sink currentVrB = VREF+200 mV, VcoMP = 1 V40µAVeg.oreError amplifier offset-10010mVVoltageComp pin source currentVrB = VREF-200 mV, VcoMP = 1 V40µAVocLPComp pin source currentVrB = VREF-200 mV, VcoMP = 1 V40µAVocLPComp pin clamp VoltageHigh Clamp3VLow ClampLow Clamp0.75VVGaaError amplifier transconductance240340440RagaError amplifier corsosver frequencyTref = 80 kΩ1.01.21.4Rreq = 80 kΩ8001.060.210.26nsRagaDim num on pulse widthRfreq = 80 kΩ1.01.21.4RagaDim num on pulse widthRfreq = 80 kΩ1.01.30.25QNetanel MoSFET on-resistanceVoVo0.30.45VVore, Vorg and Statt	V <sub>hys</sub>	Under-voltage lockout hysteresis			130		mV
Venh         EN logic high voltage         Vin = 2.9 V to 18 V         1.2         V           Vend         EN logic how voltage         Vin = 2.9 V to 18 V         -0.4         V           Ren         EN pull down resistor         400         800         1600         KΩ           Tart         Shutdown resistor         EN high to low         10         -         ms           Voltage feedback regulation voltage         EN high to low         195         200         nA           Ver         Voltage feedback regulation voltage         -         -         200         nA           Ver         Voltage feedback regulation voltage         Interventee         -         -         0         10         mV           Var         Ver         Comp pin sink current         Vr         Fe         Ver         -         40         µA           Varue         Comp pin source current         Vr         Fe         Ver         -         0         0.75         V           Votage feedback input bias current         Vr         Fe         Ver         -         0         0         95         V           VoccP         Comp pin threshold         Duity cycle o%         0.0.55         V         0         <	ENABLE AND	REFERENCE CONTROL					
Varial RanEN logic low voltageVin = 2.9 V to 18 V $-0.4$ VRanEN uld down resistor4008001600KΩToirShutdown delay, SS dischargeEN high to low10msVOLTAGE AND CURRENT CONTROL900195200205mVIrenVoltage feedback regulation voltage195200205mVIrenVoltage feedback regulation voltage-10010mVIrenVoltage feedback regulation voltage-10010mVIrenStandardVrg = VREF+200 mV, V <sub>COMP</sub> = 1 V40 $\mu$ AIgaucComp pin source currentVrg = VREF-200 mV, V <sub>COMP</sub> = 1 V40 $\mu$ AIgaucComp pin clamp VoltageHigh Clamp3VLow Clamp0.75V0.055VGeaError amplifier transconductance240340440µmhoReaError amplifier output resistance10MQ2.160.210.26Maximum duty cycleRfreq = 80 kQ1.061.21.4.1762.22.44DmaxMaximum duty cycleRfreq = 80 kQ60.035V.160.25.14DmaxMaximum duty cycleRfreq = 80 kQ1.06.1.60.25.160.25.16DmaxMaximum duty cycleRfreq = 80 kQ60.0.35V.121.4.16.25.16DmaxMaximum duty cycleRfreq = 80 kQ	V <sub>enh</sub>	EN logic high voltage	Vin = 2.9 V to 18 V	1.2			V
Ran         EN pull down resistor         400         800         1600         kΩ           T <sub>aff</sub> Shuddown delay, SS discharge         EN high to low         10         10         ms           VOLTAGE AND CURRENT CONTROL          185         200         205         mV           Vage         Voltage feedback regulation voltage         185         200         205         mV           Vage         Error amplifier offset         -10         0         10         mV           law         Comp pin sink current         VFB = VREF-200 mV, V_COMP = 1 V         40         40         µA           Voct.P         Comp pin sink current         VFB = VREF-200 mV, V_COMP = 1 V         40         40         µA           Voct.P         Comp pin clamp Voltage         High Clamp         3         V         V           Voct.P         Comp pin threshold         Duty cycle = 0%         0.95         V         V           Qr.H         Comp pin source current         VFB = VREF -200 mV, V_COMP = 1         MQ         60         KMQ           Rage         Error amplifier transconductance         0.016         0.12         0.16         MQ           Rage         Error amplifier output resistance         KTreq = 80 kΩ<	V <sub>enl</sub>	EN logic low voltage	Vin = 2.9 V to 18 V			0.4	V
Toff         Shutdown delay, SS discharge         EN high to low         10         ms           VOLTAGE AND CURRENT CONTROL         195         200         205         mV           Varge         Voltage feedback regulation voltage         195         200         205         mV           Varge         Voltage feedback regulation voltage	R <sub>en</sub>	EN pull down resistor		400	800	1600	kΩ
VOLTAGE AND CURRENT CONTROLValuage feedback regulation voltage195200205mV $l_{PB}$ Voltage feedback input bias current200nA $V_{EA, OFF}$ Error amplifier offset-10010mV $l_{sink}$ Comp pin sink current $V_{FB} = V_{REF} + 200 mV, V_{COMP} = 1 V$ 4040 $\mu$ A $l_{source}$ Comp pin source current $V_{FB} = V_{REF} - 200 mV, V_{COMP} = 1 V$ 4040 $\mu$ A $V_{CCLP}$ Comp pin clamp VoltageHigh Clamp Low Clamp0.75V $V_{CTH}$ Comp pin thresholdDuty cycle = 0%0.95V $V_{CTH}$ Comp pin thresholdDuty cycle = 0%0.95V $Q_{CH}$ Error amplifier transconductance10MQMQ $R_{a}$ Error amplifier output resistance100101214 $R_{req}$ 80 kQ0.160.210.26MHz $R_{req}$ Asimum duty cycleRfreq = 40 kQ101214 $R_{req}$ 90 kQ101214176222.64 $V_{REQ}$ FREQ µin voltageRfreq = 80 kQ60101214 $R_{req}$ Maximum duty cycleRfreq = 80 kQ6010101214 $R_{req}$ N-channel MOSFET on-resistance $V_{NI} = V_{GS} = 3.0 V$ $0.13$ 0.25 $k$ Q $V_{V_{NI} = V_{QS} = 3.0 V$ $V_{SS} = 40 V, T_A = 25^{\circ}C$ $V_{S}$ $k$ Q $V_{SV}$ $V_{SVP}$ <	T <sub>off</sub>	Shutdown delay, SS discharge	EN high to low	10			ms
VREF         Voltage feedback regulation voltage         195         200         205         mV $V_{FR}$ Voltage feedback input bias current	VOLTAGE AN	D CURRENT CONTROL					
$ \begin{array}{ c c c c c } \hline \begin{tabular}{ c c c c } \hline \begin{tabular}{ c c c c } \hline \begin{tabular}{ c c c c c c } \hline \begin{tabular}{ c c c c c c } \hline \begin{tabular}{ c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	V <sub>REF</sub>	Voltage feedback regulation voltage		195	200	205	mV
VEA_OFFError amplifier offset-10010mVIsourceComp pin sink currentVFB = VREF+200 mV, VCOMP = 1 V40 $\mu$ AIsourceComp pin source currentVFB = VREF -200 mV, VCOMP = 1 V40 $\mu$ AVCLPComp pin Clamp VoltageHigh Clamp33VLow Clamp0.75VVVGTHComp pin thresholdDuty cycle = 0%0.95VGeaError amplifier transconductance240340440 $\mu$ mhoReaError amplifier routput resistance10MQfeaError amplifier consover frequency500KHzFREQUENCYFREQUENCY1.01.20.26fsOscillator frequencyRfreq = 480 kΩ1.01.20.26Maximum duty cycleRfreq = 40 kΩ1.00.160.210.26VerReQFREQ pin voltage1.229VVTmin_onMinimum on pulse widthRfreq = 80 kΩ89%93%VVerReQFREQ pin voltage1.229VVTmin_onMinimum on pulse widthRfreq = 80 kΩ0.130.25KΩPOWER SWITCHVorse = 3.0 V0.33.3.85ALuk_NEETN-channel MOSFET on-resistanceV_N = VGS = 3.6 V0.130.25\$V_N = VGS = 3.0 V0.30.33.3.85AV_NPVOS = 40 V, T_A = 25°C1 $\mu$ AV_OVPOver voltage protection threshold0.	I <sub>FB</sub>	Voltage feedback input bias current				200	nA
$\begin{split} \begin{tabular}{ c                                   $	$V_{EA_OFF}$	Error amplifier offset		-10	0	10	mV
$\begin{array}{c c c c c c } & \begin{tabular}{c c c c c c } & \begin{tabular}{c c c c c c c } & \begin{tabular}{c c c c c c c c } & \begin{tabular}{c c c c c c c c c c c c c c c c c c c $	l <sub>sink</sub>	Comp pin sink current	$V_{FB} = V_{REF}$ +200 mV, $V_{COMP}$ = 1 V		40		μA
V_{CCLP}Comp pin Clamp VoltageHigh Clamp Low Clamp $3$ $0.75$ VV_{CTH}Comp pin thresholdDuty cycle = 0% $0.95$ VGaaError amplifier transconductance240340440µmhoReaError amplifier output resistance1010MQfeaError amplifier crossover frequency $500$ KHzFREQUENCYFREQUENCY $1.0$ $1.2$ $0.26$ MHzRifreq = 480 kQ Rifreq = 80 kQ $0.16$ $0.21$ $0.26$ $1.0$ MHz $0_{max}$ Maximum duty cycleRifreq = 40 kQ $1.0$ $1.22$ $2.64$ VFREQFREQ pin voltage $0.16$ $0.21$ $0.26$ $1.02$ $0.26$ Maximum duty cycleRifreq = 80 kQ $89\%$ $93\%$ $0.25$ VFREQFREQ pin voltage $0.16$ $0.21$ $0.26$ $0.13$ $0.25$ VFREQFREQ pin voltage $0.16$ $0.21$ $0.26$ $0.13$ $0.25$ VFREQ $V_{PEEQ}$ $FREQ pin voltage0.160.130.250.130.25QUEWENV_{IN} = V_{GS} = 3.60.130.250.130.250.13USAND0.130.250.130.250.13USAND0.160.130.250.130.25QUEWEN0.160.130.250.130.25$	Isource	Comp pin source current	$V_{FB} = V_{REF} - 200 \text{ mV}, V_{COMP} = 1 \text{ V}$		40		μA
VCTHComp pin thresholdDuty cycle = 0% $0.95$ VGeaError amplifier transconductance240340440µmhoReaError amplifier output resistance10MQfeaError amplifier crossover frequency500KHzFREQUENCYFREQUENCYFrequency8160.160.210.260.16MHzRifreq = 80 kQ0.160.210.261.01.21.4Rifreq = 40 kQ1.01.21.41.762.22.64DmaxMaximum duty cycleRifreq = 80 kQ89%93%VVFREQFREQ pin voltage1.229VVTmin_onMinimum on pulse widthRifreq = 80 kQ60nsRdim_fillDimming filter resistance25kQVPOWER SWITCHRos(ON)0.130.25QILIMN-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 V$ 0.130.25QVorVor0.30.33.85AIssSoft start bias currentVps = 40 V, T_A = 25°C1µAVovpOver voltage protection threshold1.1921.2291.266VVovpOver voltage protection threshold1.1921.2291.266VVovpOver voltage protection threshold1.1921.2291.266VVovp_thysOver voltage protec	V <sub>CCLP</sub>	Comp pin Clamp Voltage	High Clamp Low Clamp		3 0.75		V
$G_{ea}$ Error amplifier transconductance240340440µmho $R_{ea}$ Error amplifier output resistance10MQ $f_{ea}$ Error amplifier crossover frequency500KHzFREQUENCYFrequencyMfreq = 480 kQ Rfreq = 80 kQ0.160.210.26 0.12MHzMaximum duty cycleRfreq = 480 kQ Rfreq = 80 kQ0.160.210.26 0.22MHz $D_{max}$ Maximum duty cycleRfreq = 80 kQ89%93%U $V_{FREQ}$ FREQ pin voltage1.222.64V $T_{min_on}$ Minimum on pulse widthRfreq = 80 kQ89%93%UMinimum on pulse widthRfreq = 80 kQ60nsRdim, fil060nsRdim, fil00.130.25QPOWER SWITCHRos(ON)0.130.25QLI_I_N PreferN-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 V$ 0.130.25Q $V_{IN} = V_{GS} = 3.0 V$ 0.33.85A $O_{C}$ , OVP and S $V_{IN} = V_{GS} = 3.0 V$ 0.33.85A $I_{LM}$ N-channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVss = 0 V6µAV $V_{OVP}$ Over voltage protection hysteresis $V = V_{OV}$ $V_{OV}$ $V_{OV}$ $V_{OV}$	V <sub>CTH</sub>	Comp pin threshold	Duty cycle = 0%		0.95		V
$R_{ea}$ Error amplifier output resistance10MQ $f_{ea}$ Error amplifier crossover frequency500kHzFREQUENCY $f_S$ Oscillator frequencyRfreq = 480 kQ Rfreq = 80 kQ0.160.210.26 1.2MHz $P_{max}$ Maximum duty cycleRfreq = 80 kQ Rfreq = 80 kQ89%93%93% $V_{FREQ}$ FREQ pin voltage1.229VV $T_{min_on}$ Minimum on pulse widthRfreq = 80 kQ60ns $R_{dim_fil}$ Dimming filter resistance25kQPOWER SWITCH $R_{DS(ON)}$ N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 V$ 0.130.25QVIN $V_{DS} = 40 V, T_A = 25^{\circ}C$ 1 $\muA$ OC, OVP and SSILIMN-Channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVss = 0 V6 $\muA$ $V_{OVP}$ Over voltage protection threshold1.921.266V $V_{OVP_hys}$ Over voltage protection threshold1.921.266VTHERMAL SHUTDOWNTabutdown threshold hysteresis160°CTo thermal shutdown threshold hysteresis15°C	G <sub>ea</sub>	Error amplifier transconductance		240	340	440	µmho
fea         Error amplifier crossover frequency         KHz           FREQUENCY         FREQUENCY         Rfreq = 480 kΩ Rfreq = 80 kΩ         0.16         0.21         0.26         MHz           fs         Oscillator frequency         Rfreq = 480 kΩ Rfreq = 80 kΩ         0.16         0.21         0.26         MHz           Dmax         Maximum duty cycle         Rfreq = 80 kΩ         89%         93%             V         FREQ pin voltage         Rfreq = 80 kΩ         89%         93%             VFREQ         FREQ pin voltage         1.229         V	R <sub>ea</sub>	Error amplifier output resistance			10		MΩ
FREQUENCY $f_S$ Oscillator frequencyRfreq = 480 k\Omega Rfreq = 80 k\Omega0.160.210.26 0.21MHz $P_{Req}$ 80 k\Omega1.01.21.4 1.762.22.64 $D_{max}$ Maximum duty cycleRfreq = 80 k\Omega89%93% $V_{FREQ}$ FREQ pin voltage1.229VV $T_{min_on}$ Minimum on pulse widthRfreq = 80 kΩ60ns $R_{dim_fil}$ Dimming filter resistance25KΩPOWER SWITCHRog(ON)N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 V$ $V_{IN} = V_{GS} = 3.0 V$ 0.130.25 0.25 $\Omega$ $D_{LN_NFET}$ N-channel leakage current $V_{DS} = 40 V$ , $T_A = 25^{\circ}C$ 1 $\mu A$ $OC, OVP and SS$ $V_{IN} = V_{GS} = 3.0 V$ 6 $\mu A$ $I_{LN_NFET}$ N-channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVss = 0 V6 $\mu A$ $V_{OVP}$ Over voltage protection threshold1.1921.2291.266V $V_{OVP_hys}$ Over voltage protection threshold40mVmV $V_{OVP_hys}$ Over voltage protection threshold160 $^{\circ}C$ $T_{Shutdown}$ Thermal shutdown threshold160 $^{\circ}C$	f <sub>ea</sub>	Error amplifier crossover frequency			500		kHz
	FREQUENCY						
D_maxMaximum duty cycleRfreq = 80 kΩ89%93% $\begin{titered}{c} \line{1} \lin$	f <sub>S</sub>	Oscillator frequency	Rfreq = 480 kΩ Rfreq = 80 kΩ Rfreq = 40 kΩ	0.16 1.0 1.76	0.21 1.2 2.2	0.26 1.4 2.64	MHz
$V_{FREQ}$ FREQ pin voltage1.229V $T_{min_on}$ Minimum on pulse widthRfreq = 80 k $\Omega$ 60ns $R_{dim_fil}$ Dimming filter resistance25k $\Omega$ POWER SWITCH $R_{DS(ON)}$ N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6$ V0.130.25 $\Omega$ $I_{LN_NFET}$ N-channel leakage current $V_{DS} = 40$ V, $T_A = 25^{\circ}$ C0.3 $\Omega$ $OC, OVP$ and SS $I_{LM}$ N-channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVss = 0 V6 $\mu$ A $V_{OVP}$ $V_{OVP}$ voltage protection threshold1.1921.2291.266V $V_{OVP}$ Over voltage protection hysteresis40mVmVTHERMAL SHUTDOWNThermal shutdown threshold $160$ °CT_butdownThermal shutdown threshold hysteresis15°C $V_{CV}$	D <sub>max</sub>	Maximum duty cycle	Rfreq = 80 kΩ	89%	93%		
Tmin_onMinimum on pulse widthRfreq = 80 kΩ60ns $R_{dim_fil}$ Dimming filter resistance25kΩPOWER SWITCH $R_{DS(ON)}$ N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 V$ 0.130.25 $\Omega$ $N_{IN} = V_{GS} = 3.0 V$ 0.30.30.40.40.40.4 $I_{LN_NFET}$ N-channel leakage current $V_{DS} = 40 V, T_A = 25^{\circ}C$ 1 $\mu A$ OC, OVP and SSILIMN-Channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVSs = 0 V6 $\mu A$ $V_{OVP}$ Over voltage protection threshold1.1921.2291.266V $V_{OVP_hys}$ Over voltage protection hysteresis40mVThermal shutdown threshold160°CT_shutdown160°CT hermal shutdown threshold hysteresis	V <sub>FREQ</sub>	FREQ pin voltage			1.229		V
Rdim_filDimming filter resistance $L\Omega$ POWER SWITCHRDS(ON)N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 \text{ V}$ $0.13$ $0.25$ $\Omega$ $V_{IN} = V_{GS} = 3.0 \text{ V}$ $0.13$ $0.25$ $\Omega$ $\Omega$ $I_{LN_NFET}$ N-channel leakage current $V_{DS} = 40 \text{ V}, T_A = 25^{\circ}\text{C}$ $1$ $\mu A$ OC, OVP and SS $I_{LIM}$ N-Channel MOSFET current limit $D = D_{max}$ $3$ $3.8$ $5$ $A$ $I_{SS}$ Soft start bias currentVss = 0 V $6$ $\mu A$ $V_{OVP}$ Over voltage protection threshold $1.192$ $1.229$ $1.266$ $V$ $V_{OVP_hys}$ Over voltage protection hysteresis $40$ $mV$ Thermal shutdown threshold hysteresis $160$ $^{\circ}C$ T_buttoreirThermal shutdown threshold hysteresis $160$ $^{\circ}C$	T <sub>min_on</sub>	Minimum on pulse width	Rfreq = 80 k $\Omega$		60		ns
POWER SWITCH $R_{DS(ON)}$ N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 \text{ V}$ $0.13$ $0.25$ $\Omega$ $V_{IN} = V_{GS} = 3.0 \text{ V}$ $0.3$ $\Omega$ $I_{LN_NFET}$ N-channel leakage current $V_{DS} = 40 \text{ V}, T_A = 25^{\circ}\text{C}$ $1$ $\mu A$ OC, OVP and SSILIMN-Channel MOSFET current limit $D = D_{max}$ $3$ $3.8$ $5$ $A$ $I_{SS}$ Soft start bias current $Vss = 0 \text{ V}$ $6$ $\mu A$ $V_{OVP}$ Over voltage protection threshold $1.192$ $1.229$ $1.266$ $V$ $V_{OVP_hys}$ Over voltage protection hysteresis $40$ mVThermal shutdown threshold $160$ $^{\circ}C$ T shutdown $160$ $^{\circ}C$	R <sub>dim_fil</sub>	Dimming filter resistance			25		kΩ
RDS(ON)N-channel MOSFET on-resistance $V_{IN} = V_{GS} = 3.6 \text{ V}$ $0.13$ $0.25$ $\Omega$ $V_{IN} = V_{GS} = 3.0 \text{ V}$ $V_{IN} = V_{GS} = 3.0 \text{ V}$ $0.3$ $0.13$ $0.25$ $I_{LN_NFET}$ N-channel leakage current $V_{DS} = 40 \text{ V}, T_A = 25^{\circ}\text{C}$ $1$ $\mu A$ OC, OVP and SS $I_{LIM}$ N-Channel MOSFET current limit $D = D_{max}$ $3$ $3.8$ $5$ $A$ $I_{SS}$ Soft start bias currentVss = 0 V $6$ $\mu A$ $V_{OVP}$ Over voltage protection threshold $1.192$ $1.229$ $1.266$ $V$ $V_{OVP_hys}$ Over voltage protection hysteresis $40$ mVTshutdown thresholdTshutdown threshold $160$ $^{\circ}C$ T shutdown threshold hysteresis	POWER SWIT	СН					
$V_{IN} = V_{GS} = 3.0 V$ 0.3 $I_{LN\_NFET}$ N-channel leakage current $V_{DS} = 40 V, T_A = 25^{\circ}C$ 1 $\mu A$ OC, OVP and SS $I_{LIM}$ N-Channel MOSFET current limit $D = D_{max}$ 33.85A $I_{SS}$ Soft start bias currentVss = 0 V6 $\mu A$ $V_{OVP}$ Over voltage protection threshold1.1921.2291.266V $V_{OVP\_hys}$ Over voltage protection hysteresis40mVThermal shutdown thresholdTshutdown160°CT shutdown threshold hysteresisThermal shutdown threshold hysteresis	R <sub>DS(ON)</sub>	N-channel MOSFET on-resistance	$V_{IN} = V_{GS} = 3.6 V$		0.13	0.25	Ω
ILN_NFETN-channel leakage current $V_{DS} = 40 \text{ V}, T_A = 25^{\circ}\text{C}$ 1 $\mu A$ OC, OVP and SSILIMN-Channel MOSFET current limitD = D_max33.85AIssSoft start bias currentVss = 0 V6 $\mu A$ V_OVPOver voltage protection threshold1.1921.2291.266VV_OVP_hysOver voltage protection hysteresismVThERMAL SHUTDOWNT_shutdown threshold160°CT_butdownThermal shutdown threshold hysteresis15°C			$V_{IN} = V_{GS} = 3.0 \text{ V}$			0.3	
OC, OVP and SS         I <sub>LIM</sub> N-Channel MOSFET current limit       D = D <sub>max</sub> 3       3.8       5       A         I <sub>SS</sub> Soft start bias current       Vss = 0 V       6 $\mu$ A         V <sub>OVP</sub> Over voltage protection threshold       1.192       1.229       1.266       V         V <sub>OVP_hys</sub> Over voltage protection hysteresis       40       mV         Thermal shutdown threshold         Thermal shutdown threshold hysteresis         T hermal shutdown threshold hysteresis       15       °C	I <sub>LN_NFET</sub>	N-channel leakage current	$V_{DS} = 40 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}$			1	μA
ILIMN-Channel MOSFET current limitD = D_{max}33.85AISSSoft start bias currentVss = 0 V6 $\mu$ AVOVPOver voltage protection threshold1.1921.2291.266VVOVP_hysOver voltage protection hysteresis40mVThermal shutdown thresholdT_shutdown160°CT shutdown threshold hysteresisThermal shutdown threshold hysteresis	OC, OVP and	SS					
ISSSoft start bias currentVss = 0 V6 $\mu$ AVOVPOver voltage protection threshold1.1921.2291.266VVOVP_hysOver voltage protection hysteresis40mVTHERMAL SHUTDOWNT_shutdown threshold160°CT shutdown threshold hysteresis15°C	I <sub>LIM</sub>	N-Channel MOSFET current limit	D = D <sub>max</sub>	3	3.8	5	А
VOVP         Over voltage protection threshold         1.192         1.229         1.266         V           VOVP_hys         Over voltage protection hysteresis         40         mV           THERMAL SHUTDOWN           Tshutdown         Thermal shutdown threshold         160         °C           T hysteresis         Thermal shutdown threshold hysteresis         15         °C	I <sub>SS</sub>	Soft start bias current	Vss = 0 V		6		μA
V <sub>OVP_hys</sub> Over voltage protection hysteresis     40     mV       THERMAL SHUTDOWN       Tshutdown     Thermal shutdown threshold     160     °C       T hermal shutdown threshold hysteresis     15     °C	V <sub>OVP</sub>	Over voltage protection threshold		1.192	1.229	1.266	V
THERMAL SHUTDOWN         T <sub>shutdown</sub> Thermal shutdown threshold         160       °C         T hermal shutdown threshold hysteresis       15       °C	V <sub>OVP_hys</sub>	Over voltage protection hysteresis			40		mV
T <sub>shutdown</sub> Thermal shutdown threshold     160     °C       T hyperteresic     Thermal shutdown threshold hysteresis     15     °C	THERMAL SH	UTDOWN					
Thermal shutdown threshold hysteresis 15 °C	T <sub>shutdown</sub>	Thermal shutdown threshold			160		°C
Trysteresis	T <sub>hysteresis</sub>	Thermal shutdown threshold hysteresis			15		°C



#### **DEVICE INFORMATION**

#### **PIN ASSIGNMENTS**

TSSOP 14-PIN (TOP VIEW)						
sw 🗖	10	14				
sw 🗖	2	13				
	3	12	D PGND			
EN 🗖	4	11				
ss 🗖	5	10	FREQ			
DIMC 🖂	6	9	FB			
AGND	7	8				

#### **PIN FUNCTIONS**

PIN			DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
VIN	3	I	The input pin to the IC. Connect VIN to a supply voltage between 2.9V and 18V. It is acceptable for the voltage on the pin to be different from the boost power stage input for applications requiring voltage beyond VIN range.	
SW	1,2	Ι	This is the switching node of the IC. Connect SW to the switched side of the inductor.	
FB	9	Ι	Feedback pin for positive voltage regulation. A resistor connects to this pin to program LED current.	
EN	4	I	Enable pin. When the voltage of this pin falls below the enable threshold for more than 10ms, the IC turns off. This pin is also used for PWM signal input for LED brightness dimming.	
Comp	8	0	Output of the transconductance error amplifier. An external RC network is connected to this pin.	
SS	5	0	Soft start programming pin. A capacitor between the SS pin and GND pin programs soft start timing. See application section for information on how to size the SS capacitor	
FREQ	10	0	Switch frequency program pin. An external resistor is connected to this pin. See application section for information on how to size the FREQ resistor.	
AGND	7	I	Signal ground of the IC	
PGND	12–14	I	Power ground of the IC. It is connected to the source of the PWM switch.	
OVP	11	I	Over voltage protection for LED driver. The voltage is 1.229. Using a resistor divider can program the threshold of OVP.	
DIMC	6	I	Analog and PWM dimming method option pin. A capacitor connected to the pin to set the time constant of reference for analog dimming. Float this pin for PWM dimming.	
Thermal Pad			The thermal pad should be soldered to the analog ground. If possible, use thermal via to connect to top and internal ground plane layers for ideal power dissipation.	



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#### FUNCTIONAL BLOCK DIAGRAM



#### TABLE OF GRAPHS

Circuit of Figure 1; L1 = D104C2-10 $\mu$ H; D1 = SS3P6L-E3/86A, R4 = 80k $\Omega$ , C4 = 470nF, C2 = 10 $\mu$ F, LED = OSRAM LCW W5SM, ILED=400mA; unless otherwise noted		
Efficiency	VIN = 5 V, 4 LEDs, 8 LEDs, 10 LEDs	3
Efficiency	VIN = 5 V, 12 V; Vout = 8 LEDs	4
FB voltage accuracy	vs Temperature	5
Switch current limit	vs Duty cycle	6
Switch current limit	vs Temperature	7
PWM dimming	VIN = 5 V, 4 LEDs	8
PWM dimming linearity		9
Analog dimming	C5 = 1µF, VIN = 5 V, 4 LEDs	10
Analog dimming linearity		11
PWM dimming start-up	C3 = 47 nF, C5 = Float, 200 Hz with 90% duty cycle	12
Analog dimming start-up	C3 = 47 nF, C5 = 1 $\mu$ F, 5k PWM with 90% duty cycle	13





### TPS61500

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#### DETAILED DESCRIPTION

#### OPERATION

The TPS61500 integrates a 3-A/40-V low side switch FET for driving up to 10 high brightness LEDs in series. The device regulates the FB pin voltage at 200-mV with current mode PWM (pulse width modulation) control, and the LED current is sensed through a low value resistor in series with LEDs.

The PWM control circuitry turns on the switch at the beginning of each switching cycle. The input voltage is applied across the inductor and stores the energy as inductor current ramps up. During this portion of the switching cycle, the load current is provided by the output capacitor. When the inductor current rises to the threshold set by the error amplifier output, the power switch turns off and the external Schottky diode is forward biased. The inductor transfers stored energy to replenish the output capacitor and supply the load current. This operation repeats each switching cycle. As shown in the block diagram, the duty cycle of the converter is determined by the PWM control comparator which compares the error amplifier output and the current signal. The switching frequency is programmed by the external resistor.

A ramp signal from the oscillator is added to the current ramp. This slope compensation is necessary to avoid sub-harmonic oscillation that is intrinsic to the current mode control at duty cycle higher than 50%. The feedback loop regulates the FB pin to a reference voltage through an error amplifier. The output of the error amplifier is connected to the COMP pin. An external compensation network is connected to the COMP pin to optimize the feedback loop for stability and transient response.

#### SWITCHING FREQUENCY

The switch frequency is determined by a resistor connected to the FREQ pin of the TPS61500. Do not leave this pin open. A resistor must always be connected for proper operation. See Table 2 and Figure 14 for resistor values and corresponding frequencies.

<b>U</b>	2
R4 (kΩ)	f <sub>SW</sub> (kHz)
443	240
256	400
176	600
80	1200
51	2000

#### Table 2. Switching Frequency vs External Resistor



Figure 14. Switching Frequency vs External Resistor

### TPS61500

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Increasing switching frequency reduces the value of external capacitors and inductors, but also reduces the power conversion efficiency. The user should set the frequency for compromise between efficiency and solution size.

#### SOFT START

The TPS61500 has a built-in soft start circuit which significantly reduces the start-up current spike and output voltage overshoot. When the IC is enabled, an internal bias current (6-µA typically) charges a capacitor (C3) on the SS pin. The voltage at the capacitor clamps the output of the internal error amplifier that determines the duty cycle of PWM control, thereby the input inrush current is eliminated. Once the capacitor reaches 1.8-V, the soft start cycle is completed and the soft start voltage no longer clamps the error amplifier output. Refer to Figure 12 and Figure 13 for the soft start waveform. A 47-nF capacitor eliminates the output overshoot and reduces the peak inductor current for most applications.

When the EN is pulled low for 10-ms, the IC enters shutdown and the SS capacitor discharges through a  $5k\Omega$  resistor for the next soft start.

#### ENABLE AND THERMAL SHUTDOWN

The TPS61500 enters shutdown when the EN voltage is less than 0.4-V for more than 10-ms. In shutdown, the input supply current for the device is less than 1.5 $\mu$ A (max). The EN pin has an internal 800-k $\Omega$  pull down resistor to disable the device when it is floating.

An internal thermal shutdown turns off the device when the typical junction temperature of 160°C is exceeded. The IC restarts when the junction temperature drops by 15°C.

#### UNDER VOLTAGE LOCKOUT (UVLO)

An under voltage lockout prevents mis-operation of the device at input voltages below typical 2.5V. When the input voltage is below the under voltage threshold, the device remains off and the internal switch FET is turned off. The under voltage lockout threshold is set below minimum operating voltage of 2.9V to avoid any transient VIN dip triggering the UVLO and causing the device to reset. For the input voltages between UVLO threshold and 2.9V, the device maintains its operation, but the specifications are not ensured.

#### OVER VOLTAGE PROTECTION

When the FB pin is shorted to ground or an LED fails open circuit, the output voltage can increase to potentially damaging voltages. To present the IC and the output capacitor from exceeding the maximum voltage rating, utilize the OVP pin with an external resistor divider to program an OVP threshold, as shown in the typical application. The OVP pin is set at 1.229-V, and the OVP threshold should be higher than the normal operating output voltage.



where, duty is the duty cycle of the PWM signal.

The IC chops up the internal 200mV reference voltage at the duty cycle of the PWM signal. The pulsed reference voltage is then filtered by a low pass filter that is composed of an internal 25-k $\Omega$  resistor and the external capacitor C5. The output of the filter is connected to the error amplifier as the reference voltage for the FB pin. Therefore, although a PWM signal is used for brightness dimming, only the LED DC current is modulated. This eliminates the audible noise which often occurs when the LED current is pulsed during PWM dimming. Unlike other methods for filtering the PWM signal, the TPS61500's analog dimming method is independent of the PWM logic voltage level which often has large variations.

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#### APPLICATION INFORMATION

### PROGRAMMING THE OVERVOLTAGLE PROTECTION

Select the values of R1 and R2 according to Equation 1.

$$V_{\text{OVP}} = 1.229 \text{ V} \times \left(\frac{\text{R1}}{\text{R2}} + 1\right)$$

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For example, the total forward voltage of four 3-W LED is 14V, then use R1 of 120k and R2 of 10k to program the threshold of 16V. In the OVP mode, IC regulates the output voltage at the OVP threshold.

When the fault is clear and the OVP pin voltage falls 40-mV below 1.229V, IC resumes the output regulation for LED current.

#### **PROGRAMMING THE LED CURRENT**

LED current can be determined by the value of the feedback resistor R3 and the FB pin regulation voltage of 200-mV as shown in Equation 2:

$$I_{LED} = \frac{V_{FB}}{R3}$$
(2)

The output current tolerance depends on the FB accuracy and the current sensor resistor accuracy.

#### IMPLEMENTING DIMMING

Two LED current dimming methods are provided.

- 1. Floating the DIMC pin, an external PWM signal via the EN pin, providing pure PWM dimming method.
- 2. Connecting a capacitor larger than 100-nF to the DIMC pin, an external PWM signal via the EN pin, providing analog dimming.

#### **PWM Dimming Method**

LED brightness is controlled by peak LED current and duty cycle of external PWM signal. See Figure 2, Figure 8 and Figure 9 for the PWM dimming operating and linearity. Additional external switch FETs connect/disconnect LED string during PWM on/off period, shown in the typical application. Simultaneously, the TPS61500 samples and holds the COMP voltage to speed up LED current regulation during the on period. As the IC and the external switch FETs need several hundred microseconds to regulate the LED current, the frequency and minimum duty cycle of the PWM signal are application dependent. For example, 2% is the minimum duty cycle for a 200Hz PWM signal.

The PWM dimming method offers better control of color because current through LED is kept constant each cycle.

#### **Analog Dimming Method**

When capacitor C5 is connected to the DIMC pin, the FB regulation voltage is scaled proportional to the external PWM signal's duty cycle; therefore, it achieves LED brightness change, shown in Figure 1. The relationship between the duty cycle and LED current is given by Equation 3:

$$I_{LED} = \frac{V_{FB}}{R3} \times Duty$$



(3)

11

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(1)

COMPUTING THE MAXIMUM OUTPUT CURRENT

 $-\frac{1}{\left[L \times Fs \times \left(\frac{1}{Vout + Vf - Vin} + \frac{1}{Vin}\right)\right]}$ 

 $I_p$  = inductor peak to peak ripple

L = inductor value

Vf = Schottky diode forward voltage

Fs= switching frequency

Vout= output voltage =  $\Sigma V_{LEDs} + V_{REF}$ 

$$I_{LED_{max}} = \frac{Vin \times (I_{lim} - I_p/2) \times \eta}{Vout}$$

Where

Where

ILED max = maxium LED current from the boost converter  $I_{lim} = over current limit$  $V_{LED} = LED$  forward voltage at  $I_{LED}$ n = efficiency estimate based on similar applications

For instance, when VIN is 12-V. 8 LEDs output is equivalent to Vout of 24V, the inductor is 10-uH, the Schottky forward voltage is 0.4-V and the switching frequency is 1.2-MHz; then the maximum output current is around 1-A in typical condition.

For optimum performance, the value of C5 is recommended as large as possible to provide adequate filtering for

The over-current limit in a boost converter limits the maximum input current and thus maximum input power for a given input voltage. Maximum output power is less than maximum input power due to power conversion losses. Therefore, the current limit setting, input voltage, output voltage and efficiency can all change maximum current output. The current limit clamps the peak inductor current; therefore, the ripple has to be subtracted to derive maximum DC current. The ripple current is a function of switching frequency, inductor value and duty cycle. The

the PWM frequency. For example, when the PWM frequency is 5-kHz, C5 equal to 1-µF is sufficient.

following equations take into account of all the above factors for maximum output current calculation.

#### SELECTING THE INDUCTOR

The selection of the inductor affects steady state operation as well as transient behavior and loop stability. These factors make it the most important component in power regulator design. There are three important inductor specifications, inductor value, DC resistance and saturation current. Considering inductor value alone is not enough.

Inductor values can have ±20% tolerance with no current bias. When the inductor current approaches saturation level, its inductance can falls to some percentage of its 0-A value depending on how the inductor vendor defines saturation current.

Using an inductor with a smaller inductance value forces discontinuous PWM where the inductor current ramps down to zero before the end of each switching cycle. This reduces the boost converter's maximum output current, causes large input voltage ripple and reduces efficiency. In general, large inductance value provides much more output and higher conversion efficiency. Small inductance value can give better the load transient response. For these reasons, a 4.7µH to 22µH inductor value range is recommended. Table 3 lists the recommended inductor for the TPS61500.

Meanwhile, the TPS61500 can program the switching frequency. Normally, small inductance value is suitable for high frequency and vice versa. The device has built-in slope compensation to avoid sub-harmonic oscillation associated with current mode control. If the inductor value is lower than 4.7µH, the slope compensation may not be adequate, and the loop can be unstable. Therefore, customers need to verify the inductor in their application if it is different from the recommended values.

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**ISTRUMENTS** 

(4)

(5)

Part Number	L (µH)	DCR Max (mΩ)	Saturation Current (A)	Size (L × W × H mm)	VENDOR
D104C2	10	44	3.6	10.4 × 10.4 × 4.8	ТОКО
VLF10040	15	42	3.1	10.0 × 9.7 × 4.0	TDK
CDRH105RNP	22	61	2.9	10.5 × 10.3 × 5.1	Sumida
MSS1038	15	50	3.8	10.0 × 10.2 × 3.8	Coilcraft

Table 3. Recommended Inductors for TPS61500

#### SELECTING THE SCHOTTKY DIODE

The high switching frequency of the TPS61500 demands a high-speed rectification for optimum efficiency. Ensure that the diode's average and peak current rating exceed the average output current and peak inductor current. In addition, the diode's reverse breakdown voltage must exceed the switch FET rating voltage of 40V. So, the VISHAY SS3P6L-E3/86A is recommended for TPS61500. The power dissipation of the diode's package must be larger thant the  $I_{OUT(max)} \times V_D$ 

#### SELECTING THE COMPENSATION CAPACITOR AND RESISTOR

The TPS61500 has an external compensation, COMP pin, which allows the loop response to be optimized for each application. The COMP pin is the output of the internal error amplifier. An external ceramic capacitors C4 are connected to COMP pin to stabilize the feedback loop. Use 470-nF for C4.

#### SELECTING THE INPUT AND OUTPUT CAPACITOR

The output capacitor is mainly selected to meet the requirements for the output ripple and loop stability. This ripple voltage is related to the capacitor's capacitance and its equivalent series resistance (ESR). Assuming a capacitor with zero ESR, the minimum capacitance needed for a given ripple can be calculated by

$$C_{out} = \frac{(V_{out} - V_{in})I_{out}}{V_{out} \times Fs \times V_{ripple}}$$

where, Vripple = peak to peak output ripple. The additional output ripple component caused by ESR is calculated using:

$$V_{ripple}$$
 =  $I_{out} \times R_{ESR}$ 

Due to its low ESR, Vripple\_ESR can be neglected for ceramic capacitors, but must be considered if tantalum or electrolytic capacitors are used.

Care must be taken when evaluating a ceramic capacitor's derating under dc bias, aging and AC signal. For example, larger form factor capacitors (in 1206 size) have their self resonant frequencies in the range of the switching frequency. So the effective capacitance is significantly lower. The DC bias can also significantly reduce capacitance. Ceramic capacitors can loss as much as 50% of its capacitance at its rated voltage. Therefore, almost leave margin on the voltage rating to ensure adequate capacitance at the required output voltage.

The capacitor in the range of 1uF to  $4.7\mu$ F is recommended for input side. The output requires a capacitor in the range of  $1\mu$ F to  $10\mu$ F. The output capacitor affects the loop stability of the boost regulator. If the output capacitor is below the range, the boost regulator can potentially become unstable.

The popular vendors for high value ceramic capacitors are:

**TDK** (http://www.component.tdk.com/components.php) **Murata** (http://www.murata.com/cap/index.html)

#### LAYOUT CONSIDERATIONS

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As for all switching power supplies, especially those running at high switching frequency and high currents, layout is an important design step. If layout is not carefully done, the regulator could suffer from instability as well as noise problems. To maximize efficiency, switch rise and fall times are very fast. To prevent radiation of high frequency noise (eg. EMI), proper layout of the high frequency switching path is essential. Minimize the length and area of all traces connected to the SW pin and always use a ground plane under the switching regulator to minimize interplane coupling. The high current path including the switch, Schottky diode, and output capacitor, contains nanosecond rise and fall times and should be kept as short as possible. The input capacitor needs not only to be close to the VIN pin, but also to the GND pin in order to reduce the linput supply ripple.

**EXAS** 

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#### THERMAL CONSIDERATIONS

As mentioned before, the maximum IC junction temperature should be restricted to  $125^{\circ}$ C under normal operating conditions. This restriction limits the power dissipation of the TPS61500. Calculate the maximum allowable dissipation, P<sub>D</sub>(max), and keep the actual dissipation less than or equal to P<sub>D</sub>(max). The maximum-power-dissipation limit is determined using the following equation:

$$P_{D(max)} = \frac{125^{\circ}C - T_{A}}{R_{\theta JA}}$$
(8)

where,  $T_A$  is the maximum ambient temperature for the application.  $R_{\theta JA}$  is the thermal resistance junction-to-ambient given in Power Dissipation Table.

The TPS61500 comes in a thermally enhanced TSSOP package. This package includes a thermal pad that improves the thermal capabilities of the package. The  $R_{\theta JA}$  of the TSSOP package greatly depends on the PCB layout.



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#### **REVISION HISTORY**

Changes from Original	hanges from Original (December 2008) to Revision A		
Replaced the Dissipation	ation Ratings Table with the Thermal Information Table		
Changes from Revisio	n A (February 2012) to Revision B	Page	
Changed the ORDE	RING INFORMATION table PACKAGE MARKING From: TPS61500PWI	P To: 61500 2	



11-Apr-2013

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
	(1)		Drawing		Qty	(2)		(3)		(4)	
TPS61500PWP	ACTIVE	HTSSOP	PWP	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61500	Samples
TPS61500PWPR	ACTIVE	HTSSOP	PWP	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	61500	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Multiple Top-Side Markings will be inside parentheses. Only one Top-Side Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Top-Side Marking for that device.

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### PACKAGE MATERIALS INFORMATION

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#### TAPE AND REEL INFORMATION

#### REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE AND REEL INFORMATION

#### TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

*All dimensions are nominal												
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS61500PWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TEXAS INSTRUMENTS

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### PACKAGE MATERIALS INFORMATION

14-Jul-2012



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS61500PWPR	HTSSOP	PWP	14	2000	367.0	367.0	35.0

PWP (R-PDSO-G14)

PowerPAD<sup>™</sup> PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- This drawing is subject to change without notice. Β.
- C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad
- Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <a href="http://www.ti.com">http://www.ti.com</a>.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.

E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.





NOTE: A. All linear dimensions are in millimeters

PowerPAD is a trademark of Texas Instruments





NOTES:

A.

- This drawing is subject to change without notice. Β.
- Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad. C.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad D. Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.
- F.





transfer from the integrated circuit (IC). For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



NOTE: A. All linear dimensions are in millimeters A. Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments





NOTES:

A.

- This drawing is subject to change without notice. Β.
- Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad. C.
- This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad D. Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http://www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.
- F.



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